

# HRW2502B

## Silicon Schottky Barrier Diode for Rectifying

# HITACHI

Rev. 2  
Jan. 1996

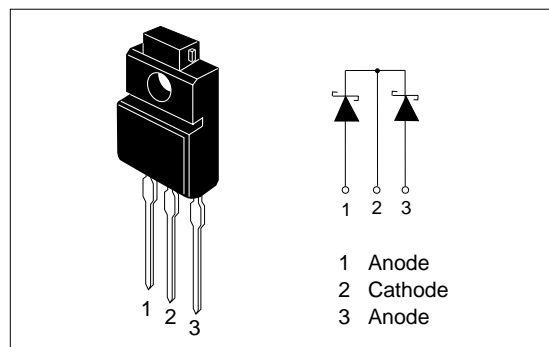
### Features

- Low forward voltage drop and suitable for high efficiency rectifying .
- Full molded fin enables easy insulation from heat sink.

### Ordering Information

Type No.	Laser Mark	Package Code
HRW2502B	W2502B	TO-220FM

### Pin Arrangement



### Absolute Maximum Ratings (Ta = 25°C) \*

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}^{**}$	20	V
Average forward current	$I_O^{***}$	25	A
Non-Repetitive peak forward surge current	$I_{FSM}^{****}$	75	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

\* Per one device

\*\* See Fig.5

\*\*\* Square wave, Duty (1/2), Sum of two devices, See Fig.4

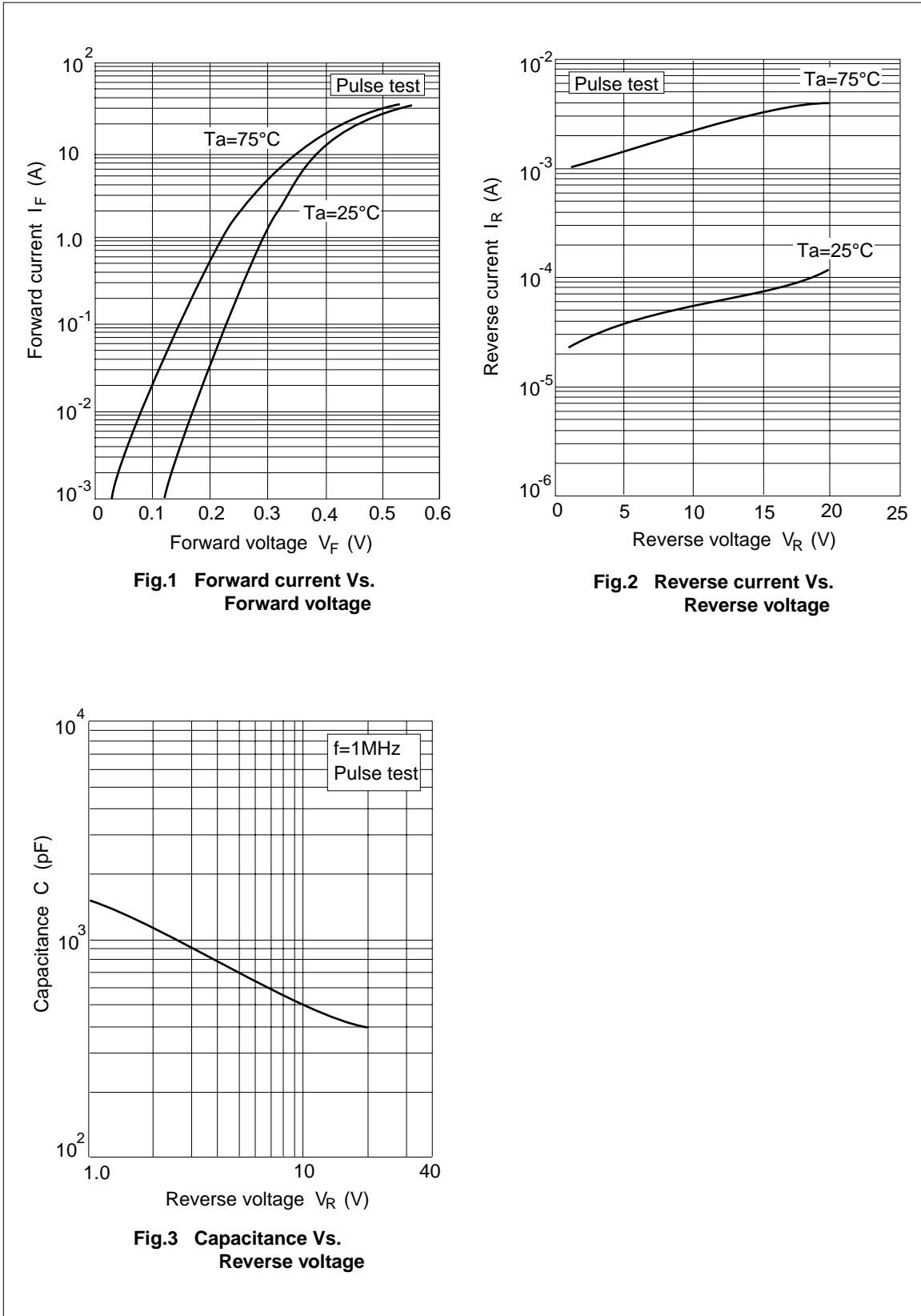
\*\*\*\* Sine wave 10msec

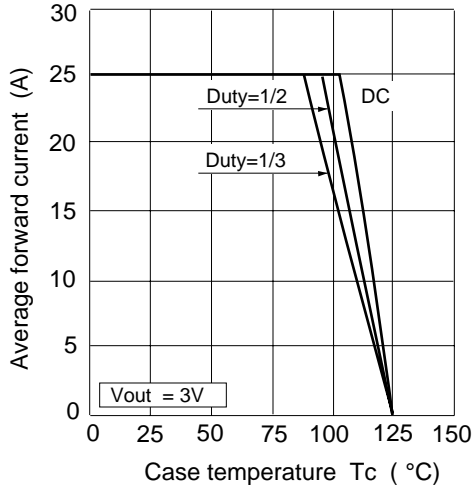
### Electrical Characteristics (Ta = 25°C) \*

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_F$	—	—	0.44	V	$I_F = 12.5 A$
Reverse current	$I_R$	—	—	1.0	mA	$V_R = 20 V$
ESD-capability	—	500	—	—	V	$C=200pF$ Both forward and reverse direction 1 pulse
Thermal resistance	$R_{th(j-c)}$	—	3.0	—	°C/W	

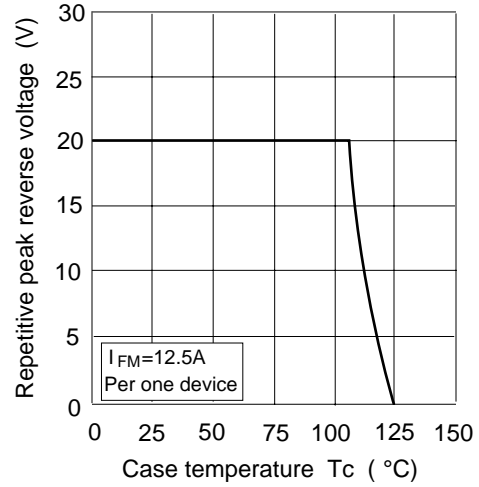
\* Per one device

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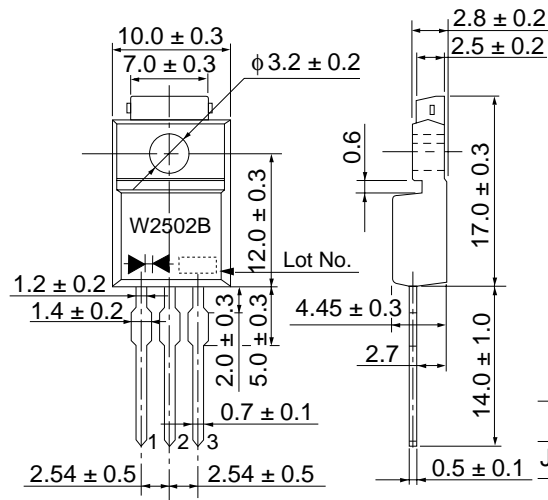
**Fig.4 Average forward current Vs. Case temperature**



**Fig.5 Repetitive peak reverse voltage Vs. Case temperature**

### Package Dimensions

Unit: mm



- 1 Anode
- 2 Cathode
- 3 Anode

HITACHI Code	TO-220FM
JEDEC Code	—
EIAJ Code	—
Weight (g)	1.8